

Page i

## **DIODES, SWITCHING**

## **BASED ON TYPE 1N5711**

## ESCC Detail Specification No. 5106/010

ISSUE 1 October 2002



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Pages 1 to 17

## **DIODES, SWITCHING**

## BASED ON TYPE 1N5711

## ESA/SCC Detail Specification No. 5106/010

# space components coordination group

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Date	SCCG Chairman	ESA Director General or his Deputy		
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ISSUE 1

PAGË 2

## **DOCUMENTATION CHANGE NOTICE**

Rev. Letter	Rev. Date	CHANGE Reference Item	Approved DCR No.
		This issue incorporates all modifications agreed on the basis of Policy DCR's 21021, 21022 and 21025	
'Α'	Aug. '88	P1. Cover page P2. DCN P8. Figure 2 : Dimension 'L' max. corrected	None None 23336
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		This document has been transferred from hardcopy to electronic format. The content is unchanged but minor differences in presentation exist.	
Ϋ́C'	Aug. '96	P1. Cover Page P2. DCN P3. T of C : Para. 1.7 entry added P5. Para. 1.7 : Paragraph added	None 21083 21083

		ESA/SCC Detail Specification No. 5106/010	Rev. 'C'	PAGÈ ISSUE	3 1
		TABLE OF CONTENTS		-	_
1.	GENERAL			F	Page 5
1.1	Scope				5
1.2	Component Type Varia	nts			5
1.3	Maximum Ratings				5
1.4	Parameter Derating Info	ormation			5
1.5	Physical Dimensions				5
1.6	Functional Diagram				5
1.7	High Temperature Test	Precautions			5
2.	APPLICABLE DOCUM	IENTS			5
3.	TERMS, DEFINITION	S, ABBREVIATIONS, SYMBOLS AND U	NITS		9
4.	REQUIREMENTS				9
4.1	General				9
4.2	Deviations from Generi	c Specification			9
4.2.1	Deviations from Specia				9
4.2.2		roduction Tests (Chart II)			9
4.2.3		and Electrical Measurements (Chart III)			9
4.2.4	Deviations from Qualific				9
4.2.5		ceptance Tests (Chart V)			9
4.3	Mechanical Requirement	nts			10
4.3.1	Dimension Check				10
4.3.2	Weight				10
4.3.3	Terminal Strength				10
4.4	Materials and Finishes				10
4.4.1	Case	h			10
4.4.2 4.5	Lead Material and Finis				10
	Marking General				11
4.5.1 4.5.2	Lead Identification				11
4.5.2 4.5.3		lumbor			11
4.5.3 4.5.4	The SCC Component N Traceability Information				11 
4.5.4 4.5.5	Marking of Small Comp			-	11 11
4.5.5	Electrical Measurement				12
4.6.1		s at Room Temperature			12
4.6.2		s at High and Low Temperatures			12
4.6.3	Circuits for Electrical M				12
					1 6

C See	ESA/SCC Detail Specification No. 5106/010		PAGE 4 ISSUE 1
-------	--	--	-------------------

		Page
4.7	Burn-in Tests	12
4.7.1	Parameter Drift Values	12
4.7.2	Conditions for Burn-in	12
4.7.3	Electrical Circuits for Burn-in	12
4.7.4	Conditions and Electrical Circuits for High Temperature Reverse Bias	12
4.8	Environmental and Endurance Tests	16
4.8.1	Electrical Measurements on Completion of Environmental Tests	16
4.8.2	Electrical Measurements at Intermediate Points and on Completion of Endurance Tests	16
4.8.3	Conditions for Operating Life Tests	16
4.8.4	Electrical Circuits for Operating Life Tests	16
4.8.5	Conditions for High Temperature Storage Test	16

#### **TABLES**

1(a)	Type Variants	6
1(b)	Maximum Ratings	6
2	Electrical Measurements at Room Temperature - d.c. Parameters	13
	Electrical Measurements at Room Temperature - a.c. Parameters	13
3	Electrical Measurements at High and Low Temperatures	15
4	Parameter Drift Values	15
5	Conditions for Burn-in	15
6	Electrical Measurements at Intermediate Points and on Completion of Endurance Testing	17

#### **FIGURES**

1	Parameter Derating Information	7
2	Physical Dimensions	8
3	Functional Diagram	8
4	Test Circuit for Measurement of Effective Carrier Lifetime	14
5	Electrical Circuits for HTRB and Burn-in	15

**APPENDICES** (Applicable to specific Manufacturers only) None.



PAGE

5

1

#### 1. <u>GENERAL</u>

#### 1.1 <u>SCOPE</u>

This specification details the ratings, physical and electrical characteristics, test and inspection data for Diodes, Switching, based on Type 1N5711.

It shall be read in conjunction with ESA/SCC Generic Specification No. 5000, the requirements of which are supplemented herein.

#### 1.2 COMPONENT TYPE VARIANTS

Variants of the basic diodes specified herein, which are also covered by this specification, are listed in Table 1(a).

#### 1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the diodes specified herein, are scheduled in Table 1(b).

#### 1.4 PARAMETER DERATING INFORMATION

The derating information applicable to the diodes specified herein is shown in Figure 1.

#### 1.5 PHYSICAL DIMENSIONS

The physical dimensions of the diodes specified herein are shown in Figure 2.

#### 1.6 <u>FUNCTIONAL DIAGRAM</u>

The functional diagram, showing lead identification, of the diodes specified herein, is shown in Figure 3.

#### 1.7 HIGH TEMPERATURE TEST PRECAUTIONS

For tin-lead plated or solder-dipped lead finish, all tests to be performed at a temperature that exceeds +125°C shall be carried out in 100% inert atmosphere.

#### 2. <u>APPLICABLE DOCUMENTS</u>

The following documents form part of this specification and shall be read in conjunction with it:-

- (a) ESA/SCC Generic Specification No. 5000 for Discrete Semiconductors.
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices.
- (c) MIL-STD-202, Test Methods for Electronic and Electrical Component Parts.



No. 5106/010

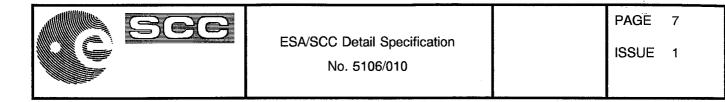
#### TABLE 1(a) - TYPE VARIANTS

Variant	Туре	Lead Material and Finish
01	1N5711	C3 or C4

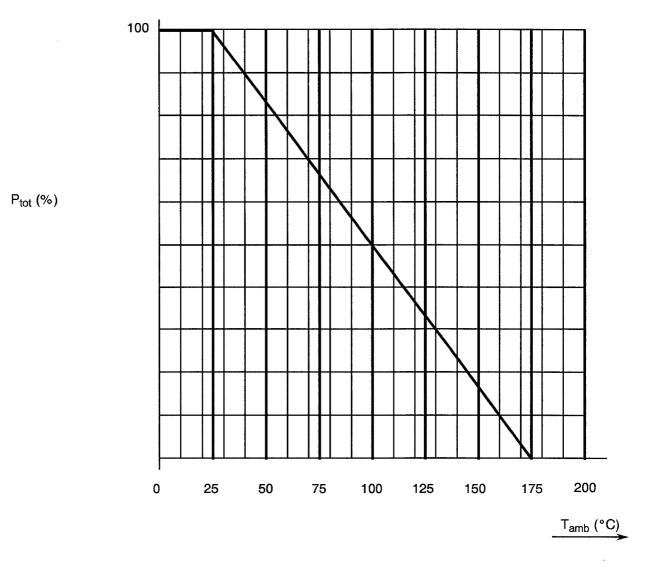
#### TABLE 1(b) - MAXIMUM RATINGS

No.	CHARACTERISTIC	SYMBOL	MAXIMUM RATING	UNIT	REMARKS
1	DC Reverse Voltage	V <sub>RM(wkg)</sub>	50	V <sub>pk</sub>	
2	Total Power Dissipation	P <sub>tot</sub>	250	mW	See Note
3	DC Forward Current	1 <sub>F</sub>	15	mA	
4	Operating Temperature Range	Т <sub>ор</sub>	– 65 to + 175	°C	T <sub>amb</sub>
5	Storage Temperature Range	T <sub>stg</sub>	- 65 to + 200	°C	
6	Soldering Temperature	T <sub>sol</sub>	+230	°C	Time: $\leq$ 10 seconds; Distance from case: $\geq$ 1.5mm
7	Average Rectified Current	lo	33	mA	

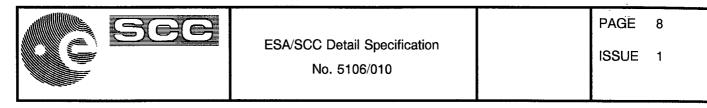
**<u>NOTES</u>** 1. At  $T_{amb}$  = +25°C. For derating above this temperature, see Figure 1.



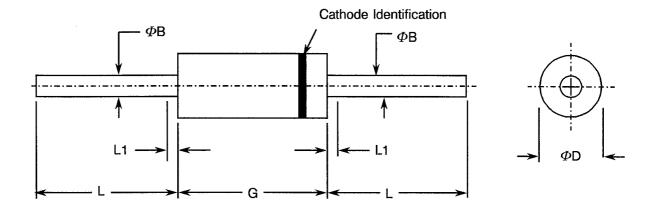
### FIGURE 1 - PARAMETER DERATING INFORMATION



Power Dissipation versus Temperature



#### FIGURE 2 - PHYSICAL DIMENSIONS



SYMBOL	INC	HES	MILLIME	TRES (3)	NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
ΦB	0.014	0.020	0.36	0.41	
ФD	0.068	0.076	1.73	1.93	1
G	0.150	0.170	3.01	4.32	1
L	1.000	1.500	25.40	38.10	
L1	-	0.050	-	1.27	2

#### **NOTES**

- 1. Package contour optional within cylinder of diameter  $\Phi$  D and length G. Slugs, if any, shall be included within this cylinder, but shall not be subject to the minimum limit of  $\Phi$  D.
- 2. Lead diameter not controlled in this zone to allow for flash, lead finish build-up and minor irregularities other than slugs.
- 3. Dimensions in millimetres are derived from original ones in inches.

#### FIGURE 3 - FUNCTIONAL DIAGRAM



#### **NOTES**

1. The cathode end shall be marked with a coloured ring.



#### 3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply.

#### 4. <u>REQUIREMENTS</u>

#### 4.1 <u>GENERAL</u>

The complete requirements for procurement of the diodes specified herein are stated in this specification and ESA/SCC Generic Specification No. 5000 for Discrete Semiconductors. Deviations from the Generic Specification applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

#### 4.2 DEVIATIONS FROM GENERIC SPECIFICATION

4.2.1 <u>Deviations from Special In-process Controls</u> None.

#### 4.2.2 Deviations from Final Production Tests (Chart II)

- (a) Para. 9.2.1, Bond Strength Test: Not applicable.
- (b) Para. 9.2.2, Die-shear Test: Not applicable.
- (c) Para. 9.7, Particle Impact Noise Detection (PIND) Test: Not applicable.
- (d) Para. 9.5, Thermal Shock Test: To be performed according to MIL-STD-202, Test Method 107, Condition 'B'.

#### 4.2.3 Deviations from Burn-in and Electrical Measurements (Chart III)

- (a) HTRB Test: Shall not be performed.
- (b) Radiographic Inspection: Not applicable.
- 4.2.4 <u>Deviations from Qualification Tests (Chart IV)</u>(a) Bond Strength and Die-shear Tests: Shall not be performed.
- 4.2.5 Deviations from Lot Acceptance Tests (Chart V) None.



Rev. 'A'

#### 4.3 MECHANICAL REQUIREMENTS

#### 4.3.1 Dimension Check

The dimensions of the diodes specified herein shall be checked. They shall conform to those shown in Figure 2.

#### 4.3.2 Weight

The maximum weight of the diodes specified herein shall be 0.25 grammes.

#### 4.3.3 <u>Terminal Strength</u>

The requirements for terminal strength testing are specified in Section 9 of ESA/SCC Generic Specification No. 5000. The test conditions shall be as follows:-

Test Condition:'A'.Applied Force:5.0 Newtons.Duration:10 seconds.

#### 4.4 MATERIALS AND FINISHES

The materials and finishes shall be as specified herein. Where a definite material is not specified, a material which will enable the diodes specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material does not guarantee acceptance of the finished product.

#### 4.4.1 <u>Case</u>

Glass, hermetically sealed.

#### 4.4.2 Lead Material and Finish

The lead material shall be Type 'C' with Type '3 or 4' finish in accordance with the requirements of ESA/SCC Basic Specification No. 23500.



#### 4.5 MARKING

#### 4.5.1 General

The marking of all components delivered to this specification shall be in accordance with the requirements of ESA/SCC Basic Specification No. 21700. Each component shall be marked in respect of:-

- (a) Lead Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

#### 4.5.2 Lead Identification

Lead identification shall be as shown in Figures 2 and 3.

#### 4.5.3 The SCC Component Number

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:

Detail Specification Number	<u>510601001B</u>
Type Variant (see Table 1(a))	
Testing Level (B or C, as applicable)	

#### 4.5.4 Traceability Information

Each component shall be marked in respect of traceability information in accordance with the requirements of ESA/SCC Basic Specification No. 21700.

#### 4.5.5 Marking of Small Components

When it is considered that the component is too small to accommodate the marking as specified above, as much as space permits shall be marked. The order of precedence shall be as follows:-

- (a) Lead Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

The marking information in full shall accompany each component in its primary package.



#### 4.6 ELECTRICAL MEASUREMENTS

#### 4.6.1 <u>Electrical Measurements at Room Temperature</u>

The parameters to be measured at room temperature are scheduled in Table 2. The measurements shall be performed at  $T_{amb}$  = +22±3 °C.

#### 4.6.2 <u>Electrical Measurements at High and Low Temperatures</u>

The parameters to be measured at high and low temperatures are scheduled in Table 3.

#### 4.6.3 Circuits for Electrical Measurements

Circuits for use in performing the electrical measurements listed in Tables 2 and 3 of this specification are shown in Figure 4.

#### 4.7 BURN-IN TESTS

#### 4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, the measurements shall be performed at  $T_{amb} = +22 \pm 3$  °C. The parameter drift values ( $\Delta$ ) applicable to the parameters scheduled, shall not be exceeded. In addition to these drift value requirements, the appropriate limit value specified for a given parameter in Table 2 shall not be exceeded.

#### 4.7.2 Conditions for Burn-in

The requirements for burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 5000. The conditions for burn-in shall be as specified in Table 5 of this specification.

#### 4.7.3 <u>Electrical Circuits for Burn-in</u>

Circuits for use in performing the burn-in tests are shown in Figure 5 of this specification.

#### 4.7.4 Conditions and Electrical Circuits for High Temperature Reverse Bias

Not applicable.



#### TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS

No.	CHARACTERISTICS	SYMBOL TEST METHOD	TEST CONDITION	LIM	UNIT		
NO.	UNANU TENIS 105	STNDOL	MIL-STD-750	TEST CONDITION	MIN.	MAX.	UNIT
1	D.C. Reverse Current	l <sub>R</sub>	4016	V <sub>R</sub> = 50V	-	200	nA
2	D.C. Forward voltage	V <sub>F</sub>	4011	I <sub>F</sub> = 1.0mA I <sub>F</sub> = 15mA	-	0.41 1.0	V
3	Breakdown Voltage	V <sub>BR</sub>	4021	l <sub>R</sub> = 10μA	70	-	V

## TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - a.c. PARAMETERS

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITION	LIMITS		UNIT
				TEST CONDITION	MIN.	MAX.	UNIT
4	Capacitance	С	MIL-STD-750 Method 4001 See Note	V <sub>R</sub> = 0V f = 1.0MHz V = 50mV max. (p.p.)	-	2.0	рF
5	Effective Carrier Lifetime	τ	Figure 4 of this specification	I <sub>F</sub> = 5.0mA Krakauer Method	-	100	ps

#### **NOTES**

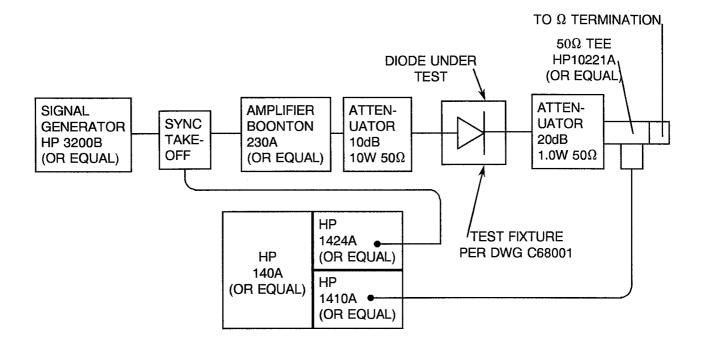
1. Sample test AQL = 2.5%.



No. 5106/010

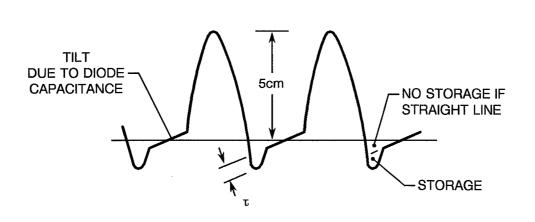
#### FIGURE 4 - TEST CIRCUIT FOR MEASUREMENT OF EFFECTIVE CARRIER LIFETIME

#### FIGURE 4(a) - TEST SET-UP FOR MEASUREMENT OF DIODE LIFETIME



This test shall be performed with the device installed in the test fixture, DESG Drawing C 68001, as per the test set-up shown in Figure 4(a). Adjust the signal generator to 54MHz and 10V output to obtain a sufficient trigger signal for the oscilloscope. Adjust the sensitivity of the oscilloscope to 10mV/cm. With the device in the test fixture, adjust the output of the amplifier until the peak amplitude of the forward current is 5.0mAdc or 2.5cm as seen on the oscilloscope. Expand pattern to 5.0cm, using the sensitivity vernier. Under these conditions, the effective carrier lifetime is related to the amplitude designated as ' $\tau$ ' shown in Figure 4(b). This amplitude has the calibration of 500ps/cm and is linear to 1.5cm.

FIGURE 4(b) - OSCILLOSCOPE DISPLAY IN MEASUREMENT OF DIODE LIFETIME





#### TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES

No.	CHARACTERISTICS	SYMBOL	MIL-STD-750 TEST METHOD	TEST CONDITION	LIMITS		UNIT
					MIN.	MAX.	
1	Reverse Current	l <sub>R</sub>	4016	V <sub>R</sub> = 50V T <sub>amb</sub> = + 150°C	-	200	μA

#### **TABLE 4 - PARAMETER DRIFT VALUES**

No.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD-750	TEST CONDITION	CHANGE LIMITS (Δ)	UNIT
1	Forward Voltage	V <sub>F</sub>	4011	l <sub>F</sub> = 1.0mAdc	±10	%
2	Reverse Current	IR	4016	V <sub>R</sub> = 50 Vdc	100 or (1) ±50	% nAdc

#### **NOTES**

1. Whichever is more referred to the initial value.

#### TABLE 5 - CONDITIONS FOR BURN-IN

No.	CHARACTERISTIC	SYMBOL	CONDITION	UNIT	
1	Working Voltage	Vr	50V (PK)	V	
2	Average Rectified Current	l <sub>o</sub>	33	mA	
3	Frequency	f	50 to 60	Hz	
4	Ambient Temperature	T <sub>amb</sub>	+ 25( + 0-3)	°C	

#### FIGURE 5 - ELECTRICAL CIRCUITS FOR HTRB AND BURN-IN

Not applicable.



#### 4.8 <u>ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESA/SCC GENERIC</u> SPECIFICATION NO. 5000)

#### 4.8.1 Electrical Measurements on Completion of Environmental Tests

The parameters to be measured on completion of environmental tests are scheduled in Table 2. The measurements shall be performed at  $T_{amb}$  = +22±3 °C.

#### 4.8.2 Electrical Measurements at Intermediate Points and on Completion of Endurance Tests

The parameters to be measured at intermediate points and on completion of endurance testing are scheduled in Table 6.

#### 4.8.3 Conditions for Operating Life Tests (Part of Endurance Testing)

The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 5000. The conditions for operating life testing shall be the same as specified in Table 5 for the burn-in test.

#### 4.8.4 Electrical Circuits for Operating Life Tests

The circuit to be used for performance of the operating life test shall be the same as shown in Figure 5 for burn-in.

#### 4.8.5 Conditions for High Temperature Storage Test (Part of Endurance Testing)

The requirements for the high temperature storage test are specified in ESA/SCC Generic Specification No. 5000. The temperature to be applied shall be the maximum storage temperature specified in Table 1(b) of this specification.



No. 5106/010

## TABLE 6 - ELECTRICAL MEASUREMENTS AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTING

No.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD-750	TEST CONDITION	LIMITS		UNIT
					MIN.	MAX.	
1	Forward Voltage	V <sub>F</sub>	4011	l <sub>F</sub> = 15mA	-	1.0	V
2	Reverse Current	l <sub>R</sub>	4016	V <sub>R</sub> = 50V	-	200	nA